## Typical Applications

## - Digital Communications Systems <br> - GSM, DCS 1800, JDC, D-AMPS Systems <br> - Spread-Spectrum Communication Systems <br> - Commercial and Consumer Systems <br> - GMSK, QPSK, DQPSK, QAM Modulation

## Product Description

The RF2422 is a monolithic integrated quadrature modulator IC capable of universal direct modulation for highfrequency AM, PM, or compound carriers. This low-cost IC implements differential amplifiers for the modulation inputs, $90^{\circ}$ carrier phase shift network, carrier limiting amplifiers, two matched double-balanced mixers, summing amplifier, and an output RF amplifier which will drive $50 \Omega$ from 800 MHz to 2500 MHz . Component matching, which can only be accomplished with monolithic construction, is used to full advantage to obtain excellent amplitude balance and phase accuracy.

Optimum Technology Matching ${ }^{\circledR}$ A pplied $\begin{array}{lll}\square \text { Si BJT } & \square \text { GaAs HBT } & \square \text { GaAs MESFET } \\ \square \text { Si Bi-CMOS } & \square \text { SiGe HBT } & \square \text { Si CMOS }\end{array}$


Functional Block Diagram


Package Style: SOIC-16

## Features

- Single 5V Power Supply
- Integrated RF Quadrature Network
- No Tuning Required
- Low LO Input Level
- Digitally Controlled Power Down Mode
- 800 MHz to 2500 MHz Operation


## Ordering Information

| RF2422 | 2.5GHz Direct Quadrature Modulator |
| :--- | :--- |
| RF2422 PCBA | Fully Assembled Evaluation Board |

RF2422

Absolute Maximum Ratings

| Parameter | Rating | Unit |
| :--- | :---: | :---: |
| Supply Voltage | -0.5 to +7.5 | $\mathrm{~V}_{\mathrm{DC}}$ |
| Input LO and RF Levels | +10 | dBm |
| Operating Ambient Temperature | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | -40 to +150 | ${ }^{\circ} \mathrm{C}$ |



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| Parameter | Specification |  |  | Unit | Condition |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Typ. | Max. |  |  |
| Carrier Input <br> Frequency Range Power Level Input VSWR | $\begin{gathered} 800 \\ -6 \end{gathered}$ | $\begin{gathered} 5: 1 \\ 1.8: 1 \\ 1.2: 1 \end{gathered}$ | $\begin{gathered} 2500 \\ +6 \end{gathered}$ | $\begin{aligned} & \mathrm{MHz} \\ & \mathrm{dBm} \end{aligned}$ | $\mathrm{T}=25^{\circ} \mathrm{C}, \mathrm{~V}_{\mathrm{CC}}=5 \mathrm{~V}$ <br> At 900 MHz <br> At 1800 MHz <br> At 2500 MHz |
| Modulation Input <br> Frequency Range Reference Voltage (VEF) Maximum Modulation (I\&Q) Gain Asymmetry Quadrature Phase Error Input Resistance Input Bias Current | $\begin{aligned} & \text { DC } \\ & 2.0 \end{aligned}$ | $\begin{gathered} 3.0 \\ \\ 0.2 \\ 3 \\ 30 \end{gathered}$ | $\begin{gathered} 250 \\ \mathrm{~V}_{\mathrm{REF}} \pm 1.0 \end{gathered}$ $40$ |  |  |
| RF Output <br> Output Power <br> Output Impedance <br> Output VSWR <br> Harmonic Output Sideband Suppression Carrier Suppression $\mathrm{IM}_{3}$ Suppression <br> Broadband Noise Floor | $-3$ <br> -30 <br> 25 <br> 30 <br> 30 <br> 25 | $\begin{gathered} 50 \\ 3.5: 1 \\ 1.3: 1 \\ 1.15: 1 \\ -35 \\ 35 \\ 35 \\ 35 \\ \\ 30 \\ \\ \\ -145 \\ -152 \\ \hline \end{gathered}$ | +3 | dBm $\Omega$ <br> dBc dB dB dB dB $\mathrm{dBm} / \mathrm{Hz}$ $\mathrm{dBm} / \mathrm{Hz}$ | $\mathrm{LO}=2 \mathrm{GHz}$ and $-5 \mathrm{dBm}, \mathrm{I} \& \mathrm{Q}=2.0 \mathrm{~V}_{\mathrm{PB}} \mathrm{SSB}$ <br> At 900 MHz <br> At 2000 MHz <br> At 2500 MHz <br> Intermodulation of the carrier and the desired RF signal <br> Intermodulation of baseband signals <br> At 20 MHz offset, $\mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V}$. <br> Tied to $\mathrm{V}_{\text {REF }}$ : ISIG, QSIG, IREF, and QREF. <br> At 850 MHz <br> At 1900 MHz |
| Power Down Turn On/Off Time PD Input Resistance Power Control "ON" Power Control "OFF" | $\begin{aligned} & 50 \\ & 1.0 \end{aligned}$ | 1.2 | 100 2.8 | $\begin{gathered} \mathrm{ns} \\ \mathrm{k} \Omega \\ \mathrm{~V} \\ \mathrm{~V} \end{gathered}$ | Threshold voltage Threshold voltage |
| Power Supply Voltage <br> Current | 4.5 | 5 45 | $\begin{aligned} & 6.0 \\ & 50 \\ & 25 \\ & \hline \end{aligned}$ | $\begin{gathered} \mathrm{V} \\ \mathrm{~V} \\ \mathrm{~mA} \\ \mu \mathrm{~A} \\ \hline \end{gathered}$ | Specifications <br> Operating Limits <br> Operating <br> Power Down |

RF2422

| Pin | Function | Description | Interface Schematic |
| :---: | :---: | :---: | :---: |
| 1 | I REF | Reference voltage for the I mixer. This voltage should be the same as the DC voltage supplied to the I SIG pin. A voltage of 3.0 V is recommended. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, the Q SIG and Q REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. This will increase the gain. |  |
| 2 | Q REF | Reference voltage for the Q mixer. This voltage should be the same as the DC voltage supplied to the Q SIG pin. A voltage of 3.0 V is recommended. |  |
| 3 | GND2 | Ground connection of the LO phase shift network. This pin should be connected directly to the ground plane. |  |
| 4 | GND2 | Same as pin 3. |  |
| 5 | GND2 | Same as pin 3. |  |
| 6 | LO | The input of the phase shifting network. This pin has an internal DCblocking capacitor. At frequencies higher than 2 GHz this port is wellmatched to $50 \Omega$. This port is voltage driven so matching at lower frequencies is not required. | LO O-mb |
| 7 | VCC1 | Power supply for all circuits except the RF output stage. An external capacitor is needed if no other low frequency bypass capacitor is nearby. |  |
| 8 | PD | Power Down control. When this pin is "low", all circuits are shut off. A "low" is typically 1.2 V or less at room temperature. When this pin is "high" ( $\mathrm{V}_{\mathrm{CC}}$ ), all circuits are operating normally. If PD is below $\mathrm{V}_{\mathrm{CC}}$, output power and performance will be degraded. Operating in this region is not recommended, although it might be useful in some applications where power control is required. |  |
| 9 | RF OUT | This is the $50 \Omega$ RF Output. This pin has an internal DC-blocking capacitor. At frequencies higher than 2 GHz this port is well-matched. Typical impedances at lower frequencies are: $24-\mathrm{j} 30 \Omega$ @ 1GHz, 27-j10 $\Omega$ @ $1.4 \mathrm{GHz}, 31-\mathrm{j} 3 \Omega @ 1.8 \mathrm{GHz}$. At those frequencies, external matching may be needed to optimize output power. |  |
| 10 | GND3 | Ground connection for the RF output stage. This pin should be connected directly to the ground plane. |  |
| 11 | VCC2 | Power supply for the RF Output amplifier. An external capacitor is needed if no other low frequency bypass capacitor is near by. |  |
| 12 | GND1 | Ground connection for the LO and baseband amplifiers, and for the mixers. This pin should be connected directly to the ground plane. |  |
| 13 | GND1 | Same as pin 12. |  |
| 14 | GND1 | Same as pin 12. |  |
| 15 | Q SIG | Baseband input to the Q mixer. This pin is DC-coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 2 V . The recommended DC level for this pin is 3.0 V . The peak minimum voltage on this pin ( $\mathrm{V}_{\text {REF }}$ - peak modulation amplitude) should never drop below 2.0 V . The peak maximum voltage on this pin ( $\mathrm{V}_{\text {REF }}+$ peak modulation amplitude) should never exceed 4.0 V . | See pin 2. |

RF2422

| Pin | Function | Description | Interface Schematic |
| :---: | :---: | :--- | :--- |
| $\mathbf{1 6}$ | I SIG | Baseband input to the I mixer. This pin is DC-coupled. Maximum output <br> power is obtained when the input signal has a peak to peak amplitude <br> of 2V. The recommended DC level for this pin is 3.0V. The peak mini- <br> mum voltage on this pin (V $\mathrm{V}_{\text {REF }}$ - peak modulation amplitude) should <br> never drop below 2.0V. The peak maximum voltage on this pin (VEF + <br> peak modulation amplitude) should never exceed 4.0V. | See pin 1. |

## Application Schematic AC-Coupled



## Application Schematic DC-Coupled



## Evaluation Board Schematic

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1.5^{\prime \prime} \times 1.5^{\prime \prime}
$$

(Download Bill of Materials from www.rfmd.com.)


Evaluation Board Layout Board Size 1.510" x 1.510"<br>Board Thickness 0.031", Board Material FR-4



